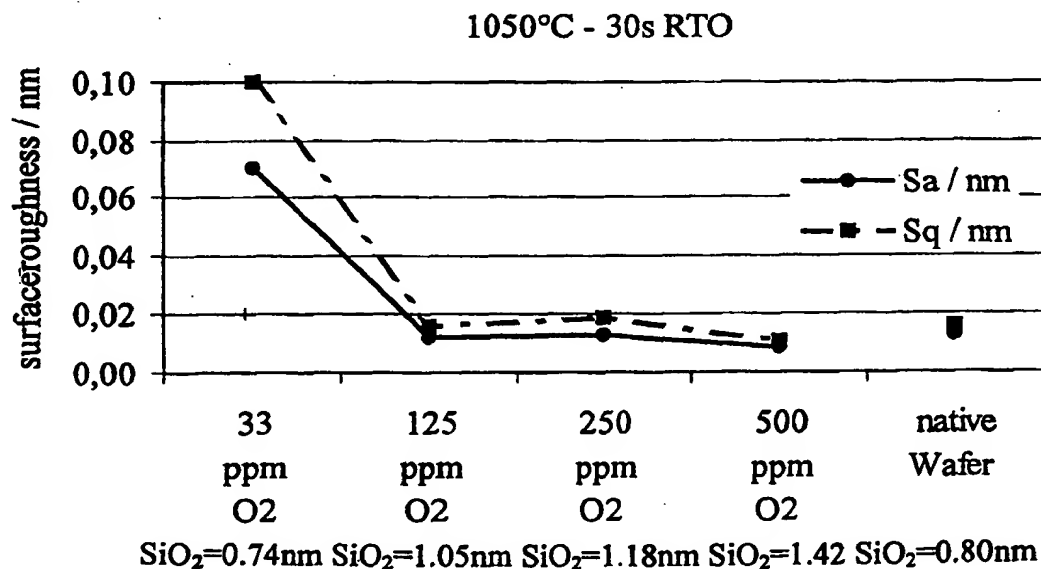




INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶ : H01L 21/28, 21/324		A1	(11) International Publication Number: WO 99/01895
			(43) International Publication Date: 14 January 1999 (14.01.99)
(21) International Application Number: PCT/EP98/03885		(81) Designated States: JP, KR, SG, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).	
(22) International Filing Date: 25 June 1998 (25.06.98)			
(30) Priority Data: 08/886,215 1 July 1997 (01.07.97) US		Published With international search report. Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.	
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(54) Title: METHOD FOR RAPID THERMAL PROCESSING (RTP) OF A SILICON SUBSTRATE



(57) Abstract

A method of rapid thermal processing (RTP) of a silicon substrate is presented, where a very low partial pressure of reactive gas is used to control etching and growth of oxides on the silicon surface.

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Method for Rapid Thermal Processing (RTP) of a Silicon Substrate

1. Field of the invention.

The present invention relates to a method for the rapid thermal processing (RTP) of sensitive electronic materials.

2. Background of the invention.

Rapid Thermal Processing (RTP) is a versatile optical heating method which can be used for semiconductor processing as well as a general, well controlled, method for heating objects or wafers which are in the form of thin sheets, slabs, or disks. The objects are generally inserted one at a time into a chamber which has at least some portions of the chamber walls transparent to transmit radiation from powerful heating lamps. The transparent portion of the walls is generally quartz, which will transmit radiation up to a wavelength of 3 to 4 microns. These lamps are generally tungsten-halogen lamps, but arc lamps or any other source of visible and/or near infrared radiation may be used. The radiation from the lamps is directed through the transparent portions of the walls on to the flat surface of the object to be heated. Radiation may be directed on to the flat surface of the object from one side or the other, or both sides simultaneously. As long as the objects absorb light in the near infrared or visible spectral region transmitted by the transparent portion of the walls, RTP techniques allow fast changes in the temperature and process gas for the different material processes and conditions. Since the flat surface of a semiconductor wafer may be uniformly irradiated, the entire wafer may be heated with relatively little temperature difference across the wafer during the entire time of heating, and hence little slip occurs. RTP allows the „thermal budgets“ of the various semiconductor processing to be reduced, as well as allows the production of various metastable states which can be „frozen in“ when the material is cooled rapidly.

1 RTP systems are relatively new. In the last 10 or 15 years, such systems were used only
in research and development. The thrust of the work was increasing the temperature
uniformity, and developing heating cycles and processes which decreased the thermal
5 budget. Prior art RTP machines can heat unstructured, homogeneous materials in the
form of a flat plate or disk, and produce temperature uniformities across the plate
adequate for semiconductor processing processes.

The temperature control in current RTP systems is mostly performed by monochromatic
10 (or narrow wavelength band) pyrometry measuring temperature of the relatively
unstructured and featureless backside of semiconductor wafers. The results of the
temperature measurement are generally used in a feedback control to control the heating
lamp power. Backside coated wafers with varying emissivity can not be used in this
15 way, however, and the backside layers are normally etched away or the temperature is
measured using contact thermocouples.

A newer method of temperature control is the power controlled open loop heating
described in U.S. Patent No. 5,359,693, which patent is hereby incorporated by
reference.

20 German patent DE 42 23 133 C2, hereby incorporated by reference, discloses a method
of producing relatively defect free material in RTP machines. Apparatus induced
thermal inhomogeneities have been reduced in the last few years because of the demand
for more uniform processing. Among the techniques used have been control of the
25 individual lamp power, use of circular lamps, and rotation of the semiconductor wafers
with independent power control.

Most RTP machines have a thin rectangular quartz reaction chamber having one end
open. Chambers meant for vacuum use often have a flattened oval cross section.

30 Chambers could even be made in the form of a flat cylindrical pancake. In general, the
chambers are used so that the thin objects to be heated are held horizontally, but they
could also be held vertical or in any convenient orientation. The reactor chamber is
usually thin to bring the lamps close to the object to be heated. The reactor chamber is
35 opened and closed at one end with a pneumatically operated door when the wafer
handling system is in operation. The door is usually made of stainless steel, and may

1 have a quartz plate attached to the inside. The process gas is introduced into the
chamber on the side opposite the door and exhausted on the door side. The process gas
flow is controlled by computer controlled valves connected to various manifolds in a
5 manner well known in the art.

In the march of semiconductor technology to ever smaller device dimensions and ever
larger wafer sizes, the depths of implant of dopant atoms is getting more and more
shallow, and the allowed tolerances for implant dose and movement of these dopant
atoms is getting tighter and tighter. Rapid thermal processing has allowed engineers to
10 keep to the tighter tolerances since the processing can be done at the optimum
temperature for the particular process, while spending very little time at other
temperatures on the way up and on the way down in the temperature vs time curve.

We have found, however, a previously unrecognized problem in the processing of
15 silicon devices having bare silicon surfaces, or only a native oxide or with very thin gate
and tunnel oxides. The processing itself seems to change the distribution and the amount
of dopant in some cases. We have found that previous process gas compositions
sometimes lead to such problems, and that proper specification of the process gas
20 composition for each particular type of wafer, temperature, and time combination, can
result in much improved uniformity of the devices produced using the RTP process.

3. Related Applications.

25 Reactors based on the RTP principle often have the entire cross section of one end of the
reactor chamber open during the wafer handling process. This construction has been
established because the various wafer holders, guard rings, and gas distribution plates,
30 which have significantly greater dimensions and may be thicker than the wafers, must
also be introduced into the chamber and must be easily and quickly changed when the
process is changed or when different wafer sizes, for example, are used. The reaction
chamber dimensions are designed with these ancillary pieces in mind. Patent application
08/387,220, now patent no. US, assigned to the assignee of the present invention and
35 hereby incorporated by reference, teaches the importance of the gas flow and the use of

1 an aperture in the door to regulate gas flow and control impurities in the process chamber.

5 The wafer to be heated in a conventional RTP system typically rests on a plurality of quartz pins which hold the wafer accurately parallel to the reflector walls of the system. Prior art systems have rested the wafer on an instrumented susceptor, typically a uniform silicon wafer.

10 Copending patent application 08/537,409, assigned to the assignee of the present invention, hereby incorporated by reference, teaches the importance susceptor plates separated from the wafer.

15 Rapid thermal processing of III-IV semiconductors have not been as successful as RTP of silicon. One reason for this is that the surface has a relatively high vapor pressure of, for example, arsenic (As) in the case of gallium arsenide (GaAs). The surface region becomes depleted of As, and the material quality suffers. Copending patent application 08/631,265, assigned to the assignee of the present invention, hereby incorporated by reference, supplies a method and apparatus for overcoming this problem.

20 OBJECTS OF THE INVENTION

It is an object of the invention to provide a method of processing a semiconductor substrate so that tolerances for dopant amount and dopant position can be met.

25 It is an object of the invention to provide a method of processing a semiconductor substrate so that very thin oxides may be produced with excellent characteristics and with excellent uniformity.

30 It is an object of the invention to provide a method of processing a semiconductor substrate so that etching a reactions of silicon and silicon oxide can be carefully controlled.

SUMMARY OF THE INVENTION

35 The atmosphere surrounding a semiconductor substrate that is being rapidly thermally processed is carefully controlled so that a very small concentration of a reactant gas is

1 used to stabilize the surface against excessive etching of the semiconductor and the thin
oxides of the semiconductor, and against excessive growth of the semiconductor oxide.

5 BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 shows the surface roughness of a wafer annealed for 30 sec at 1050C as a
function of amount of oxygen gas in a neutral ambient gas near 1 atmosphere
pressure.

10 Fig. 2 shows the surface roughness of a wafer annealed for 30 sec at 1100C as a
function of amount of oxygen gas in a neutral ambient gas near 1 atmosphere
pressure.

15 Fig. 3 shows the surface roughness of a wafer annealed for 30 sec at 1150C as a
function of amount of oxygen gas in a neutral ambient gas near 1 atmosphere
pressure.

Fig. 4 shows an atomic force microscope picture of the surface roughness of a wafer
annealed for 30 sec at 1100C in 500 ppm oxygen gas.

20 Fig. 5 shows the surface roughness of a wafer annealed for 30 sec at 1100C in 250 ppm
oxygen gas.

DETAILED DESCRIPTION OF THE INVENTION

Silicon and SiO₂ interface chemistry

25 The chemical basis of the monolithic planar IC technology is that silicon reacts at high
temperature with oxygen and the oxide (SiO₂), developed during the reaction, is a stable
and uniform layer which protects the silicon surface and acts as a barrier against dopant
diffusion. This oxide is called a thermal oxide to distinguish it from the oxide that forms
30 on clean silicon at low temperatures which is called a „native oxide“. A native oxide is
not as „good“ as a thermal oxide because the native oxide has many more states, or
„dangling bonds“, at the Si – SiO₂ interface. For completeness, a „good“ oxide may be
produced by chemical vapor deposition where little or no silicon from the interface is
consumed. It has been discovered lately that, for RTP, the high temperature, short time
35 Si – SiO₂ interface chemistry needs to be carefully evaluated in the low oxygen

1 concentration range. What is more, the chemistry plays an important role even in case of
UHV or neutral gas ambient annealing when oxide layers occur on the silicon surface or
a Si – SiO₂ interface occurs on the device.

5 Depending on several factors (most importantly on temperature and oxygen
concentration) silicon can have the following reactions with oxygen in a neutral
atmospheric pressure ambient. At the „higher“ partial pressures of oxygen



In order to produce SiO₂ on the silicon surface, there must be a minimum oxygen
concentration in an atmospheric neutral gas ambient. The minimum O₂ concentration
depends, however, strongly on temperature, dopant concentration and wafer orientation
15 and is about 500 ppm for relatively high temperatures above about 1100C. (In case of
low pressure (lower than atmospheric pressure) processes the corresponding partial
pressure of the oxygen must be used. At one atmosphere ambient pressure, 500 ppm
oxygen corresponds to a partial pressure of 0.38 torr.) The oxygen at the SiO₂ gas
20 interface migrates through the oxide and reacts at the Si – SiO₂ interface to form SiO₂.
At pressures of oxygen just above the minimum for producing SiO₂, the rate at which
the SiO₂ is formed increases slowly with the concentration of oxygen.
At lower concentrations of oxygen.



In the case of very low oxygen concentration the silicon can not be oxidized to form SiO₂, as
30 only silicon monoxide (SiO) forms. At temperatures above 900C SiO is volatile and escapes
from the surface immediately. Any open silicon surface areas, even those which are covered
with a native oxide, are etched by this reaction and silicon is consumed. We have found that the
atomic surface roughness, grows, that shallow implanted layers can partly or totally disappear
and that SiO is deposited on the cooler parts of the reactor. For ultra shallow implanted regions
35 such as regions implanted with boron, the thickness of the implanted region becomes smaller as
the silicon is etched away, and the total amount of boron in the region becomes less as the

1 boron seems to leave with the silicon. At the Si – SiO₂ interface at such low partial pressures of oxygen,



On silicon surface parts where thermal SiO₂ is present, even if its thickness is only 10nm, the thermal SiO₂ protects the surface from being etched macroscopically.

10 However, Si atoms leave the Si – SiO₂ interface. The protective SiO₂ layer however cannot stop reaction c) at the interface. Dangling bonds will be created at the Si-SiO₂ interface and in the worst case micro voids and even pitting may appear.

We have found that we can control the above mentioned processes by using a very small concentration of reactive gases in the process gas when the silicon substrate is processed at high temperatures and short times. The minimum oxygen concentration, which can protect the interface from disproportioning, depends on several factors. These are e.g. wafer temperature, local oxide thickness, doping level at the silicon surface and other components in the process gas. Such as NH₃, H₂, H₂O, N₂, NO, NO₂, Ar, etc.

20 It is important to note that all high temperature annealing steps, performed in an oxygen free ambient (also high and ultra high vacuum), lead to a certain degree of disproportioning at the Si – SiO₂ interface. Therefore, all post oxidation annealing steps must use at least a ppm level of reactive gases such as those noted.

25 Interface engineering

A detailed study of the interface reactions is particularly important for shallow and ultrashallow junction formation, for gate oxide formation and e.g. in case of boron phosphorosilicate glass (BPSG) reflow when open windows are present in thick oxide on the wafer. In order to maintain the implanted shallow dopant profiles, process engineers often have to balance on the edge of the knife: bare silicon surface parts are neither to be oxidized nor allowed to be etched. Oxidation leads to dopant segregation and anomalous diffusion. SiO creation results in etched surface and we deplete or remove the implanted surface layer. We have to find a process window in the oxygen

1 concentration where the silicon surface reactions are in a balance and only a few SiO₂ monolayers (2-3) grow on to the surface.

The oxide growth can be controlled by ellipsometrical measurement of the very thin
5 oxide layer. Any surface etch by SiO creation can be revealed by atomic surface roughness measurements.

Experimental procedure:

10 We annealed silicon wafers in AST-SHS-2800 rapid thermal system at different temperatures and in N₂ ambient at different, very low oxygen concentrations. After annealing we measured the surface roughness by SFM (scanning force microscopy) to find out which oxygen concentration results in maximum surface roughness and what the minimum required oxygen concentration is to avoid surface etching. The SHS 2800
15 RTP system can control process gas mixtures in ppm level.

The wafer specification for these experiments was: 150 mm prime CZ silicon wafer, 3-9 ohm-cm, n-type (100) orientation, from a freshly opened box. We did not use precleaning. The samples were annealed at 1050°C, 1100°C, and 1150°C for 30 sec. We
20 changed the oxygen concentration for each experiment and used 33, 125, 250, 500 and 1000 ppm O₂ levels in a neutral gas with total pressure slightly exceeding one atmosphere. For the SFM investigations we used a Topometrix Explorer head and various tips. We performed the measurements in non-contact-mode. The roughness
25 parameters were calculated from 1x1 um spots. The average Sq (root mean square deviation of the surface) and Sa (arithmetic mean deviation of the surface) of the different experiments are plotted in Fig. 1, Fig. 2, and Fig. 3 for 30 sec anneals at 1050C, 1100C, and 1150C respectively. We illustrate the SFM surface characteristics
30 after 1100°C-30s rapid thermal oxidization (RTO) in cases of 250 ppm and 500 ppm oxygen concentration in Fig. 4 and 5, respectively.

1 From our measurements we conclude the following:

- 5 a) We can safely oxidize bare silicon wafers to SiO_2 , at 1100°C and 1150°C when the annealing atmosphere contains at least 500 ppm (a partial pressure of 0.38 Torr) O_2 . The minimum partial pressure necessary to produce the oxides and not etch the native oxide surfaces may be easily determined for the various combinations of temperature and process gas components by methods as shown above.
- 10 b) At 1100°C and 1150°C we observed the strongest surface etch at 250 ppm O_2 concentration.
- c) At higher temperature the surface etch is much stronger.
- d) At 1050°C SiO_2 was created already at 125 ppm O_2 concentration. Surface etching took place at a lower oxygen level.
- 15 e) Thin oxide layers grow on implanted Si surfaces at a rate up to 1,5 – 2 times as fast as on bare silicon.
- f) In case of implanted wafers which do not have screen oxidized, we can expect, under common annealing conditions (and above 900°C), a surface etch in the range of 1-100 ppm oxygen concentration. In such cases the mean sheet resistivity grows and the uniformity becomes worse. A formal ellipsometrical measurement of the native oxide distribution can also reveal surface etch. As the surface etches the native oxide uniformity becomes worse.
- 20 g) It is surprising how suddenly the Si- SiO_2 interface becomes „self curing“ above a minimum oxygen concentration in the sub 1000 ppm level. Ultrathin SiO_2 layers of excellent quality and uniformity can be produced using high temperatures and very low oxygen concentrations. The native oxide can be cleaned off the wafer with a quick dip in HF, and the wafer surface remains passivated with H atoms for some time. When the wafer is then inserted into and heated in the RTP system with oxygen or an oxygen containing gas having a concentration above a minimum set by the temperature and other components of process gas, the wafer surface oxidizes and well controlled thickness of oxide in the range of a few monolayers to 5 nm can be reliably produced.
- 25
- 30
- 35

- 1 h) Near surface Si atoms which are energetically at different levels are oxidized more
uniformly at higher temperature. The ultrathin thickness e.g. in 0,5 – 5nm range can
be maintained by very low oxygen concentration either in low pressure or in neutral
5 gas ambient such as nitrogen or argon. Controlled thermal kinetic processing
method supports this technology.
- i) Oxygen containing gases such as H₂O, NO, NO₂, have been tried, and show similar
protective behavior as oxygen at low concentrations. Higher temperatures of 1200C
and 1250C have also been tried and show similar behavior.
- 10 j) For each RTP process temperature, there exists a minimum level of oxygen or other
reactive gas in the process gas which protects surface oxides and Si-SiO₂ interfaces
from degradation. This level is best set by experimentation as set out in the
preceding specification. The level is preferably between 0.01 Torr and 3 Torr partial
15 pressure of Oxygen. The level is more preferably between 0.1 Torr and 1 Torr
oxygen gas. Other reactive gases which we have tried include NH₃, H₂, H₂O, N₂,
NO, NO₂. We expect that all reactive gases which react with silicon will give
excellent and reproducible results when used at such low concentrations. This is
20 especially important for oxynitride production, where a ratio of one atom of nitrogen
to 100 atoms of oxygen at the Si – SiO₂ interface has been shown to be very
valuable in E²PROM production.
- k) Very low concentrations of NH₃ have been shown to have very well controlled
25 etching characteristics.

30

35

1 We claim:

- 5 1. A method of rapid thermal processing of a silicon substrate, comprising processing the silicon substrate in an RTP system in an atmosphere comprising a low concentration of reactive gas.
- 10 2. The method of claim 1, wherein the low concentration of reactive gas is between 0.01 Torr and 3 Torr partial pressure oxygen gas.
- 15 3. The method of claim 2, wherein the low concentration of reactive gas is between 0.1 Torr and 1 Torr partial pressure oxygen gas.
- 20 4. The method of claim 1, wherein the low concentration of reactive gas is between 0.01 Torr and 3 Torr partial pressure nitric oxide (NO) or nitrous oxide (N₂O).
- 25 5. The method of claim 4, wherein the atmosphere further comprises between 0.01 Torr and 3 Torr partial pressure oxygen gas.
- 30 6. The method of claim 5, wherein the partial pressure of oxygen gas is between 0.1 Torr and 1 Torr.
- 35 7. The method of claim 6, wherein the partial pressure of nitric oxide (NO) or nitrous oxide (N₂O) is between 0.1 Torr and 1 Torr partial pressure.
8. The method of claim 1, wherein the low concentration of reactive gas is between 0.01 Torr and 3 Torr partial pressure NH₃.
9. A method of RTP, comprising processing an oxidized silicon substrate in an RTP system in an atmosphere

1 containing substantially an amount of reactive gas necessary to minimize etching
of the oxidized silicon substrate.

5 10. A method of RTP, comprising
processing an oxidized silicon substrate in an RTP system in an atmosphere
containing less than a minimum amount of reactive gas necessary to minimize
etching of the oxidized silicon substrate.

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09. 10. 1998

1050°C - 30s RTO

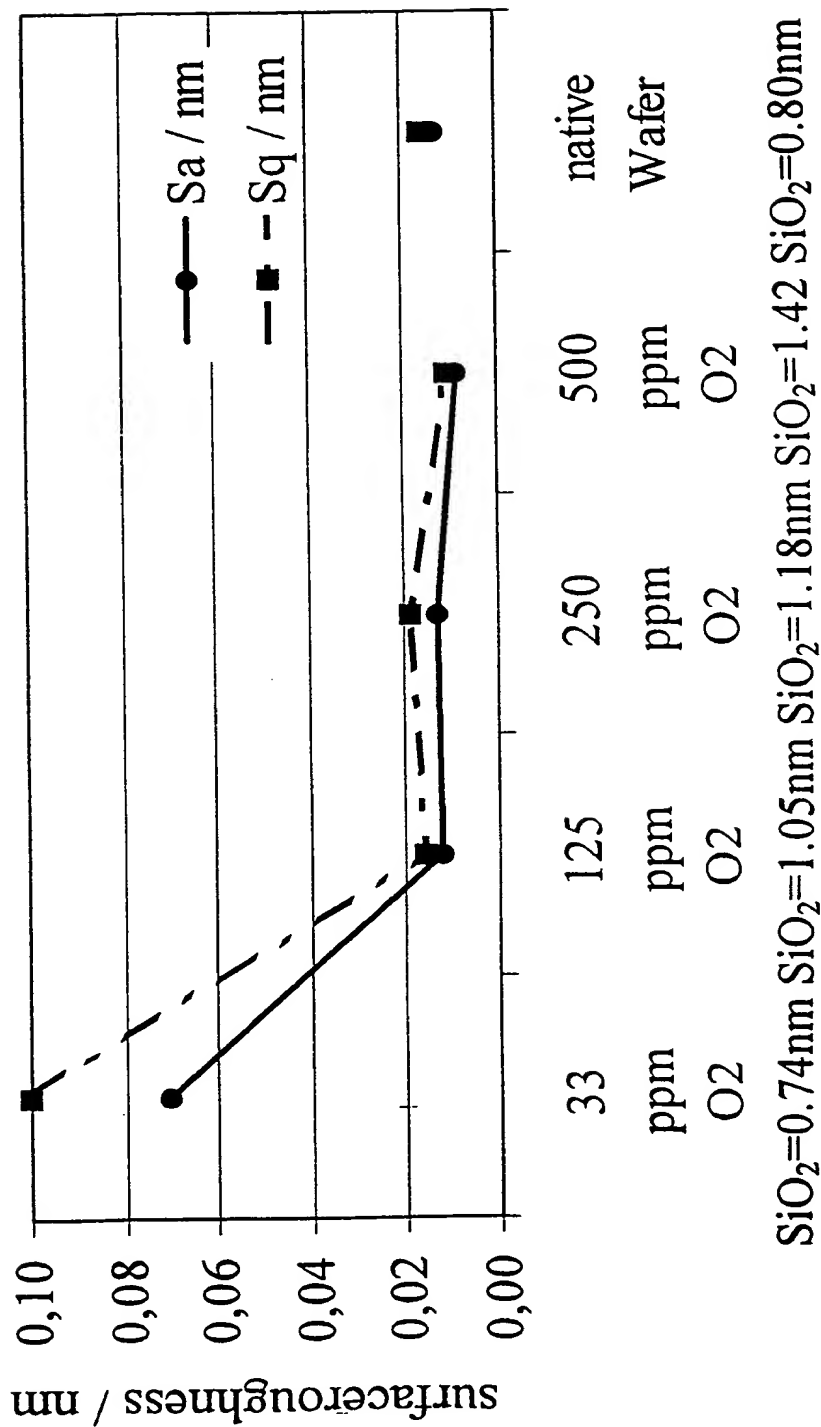


Fig. 1

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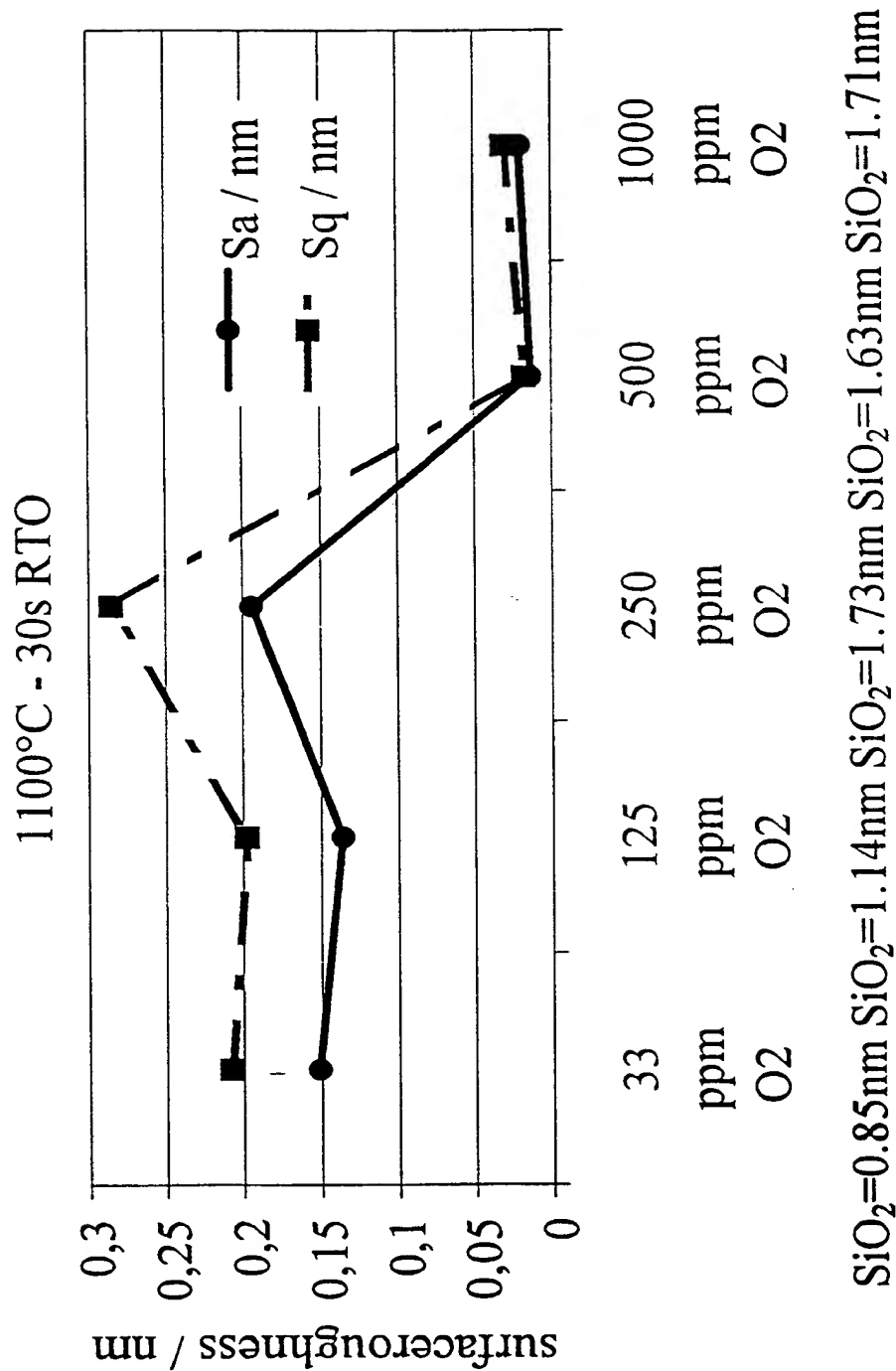


Fig. 2

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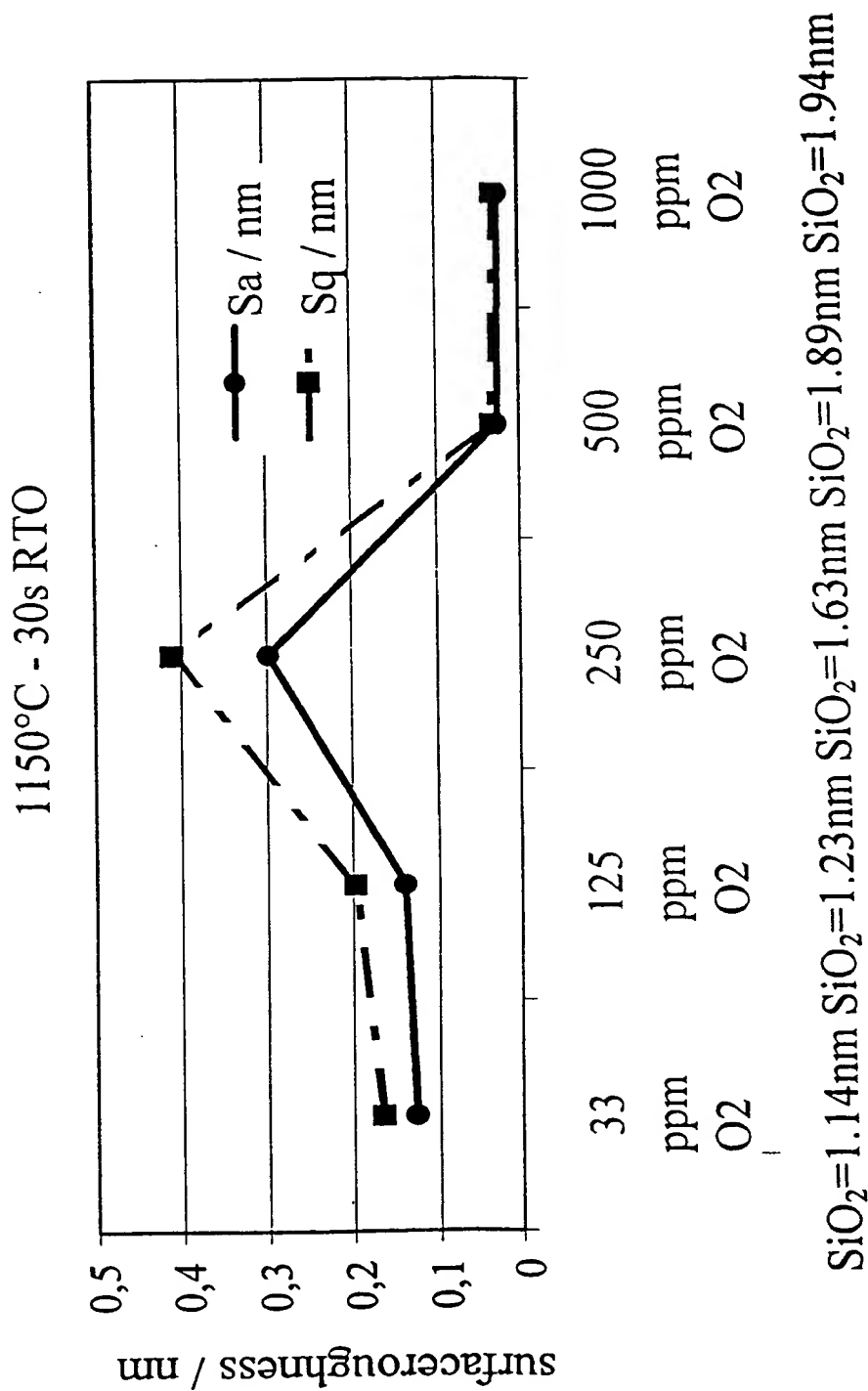


Fig. 3

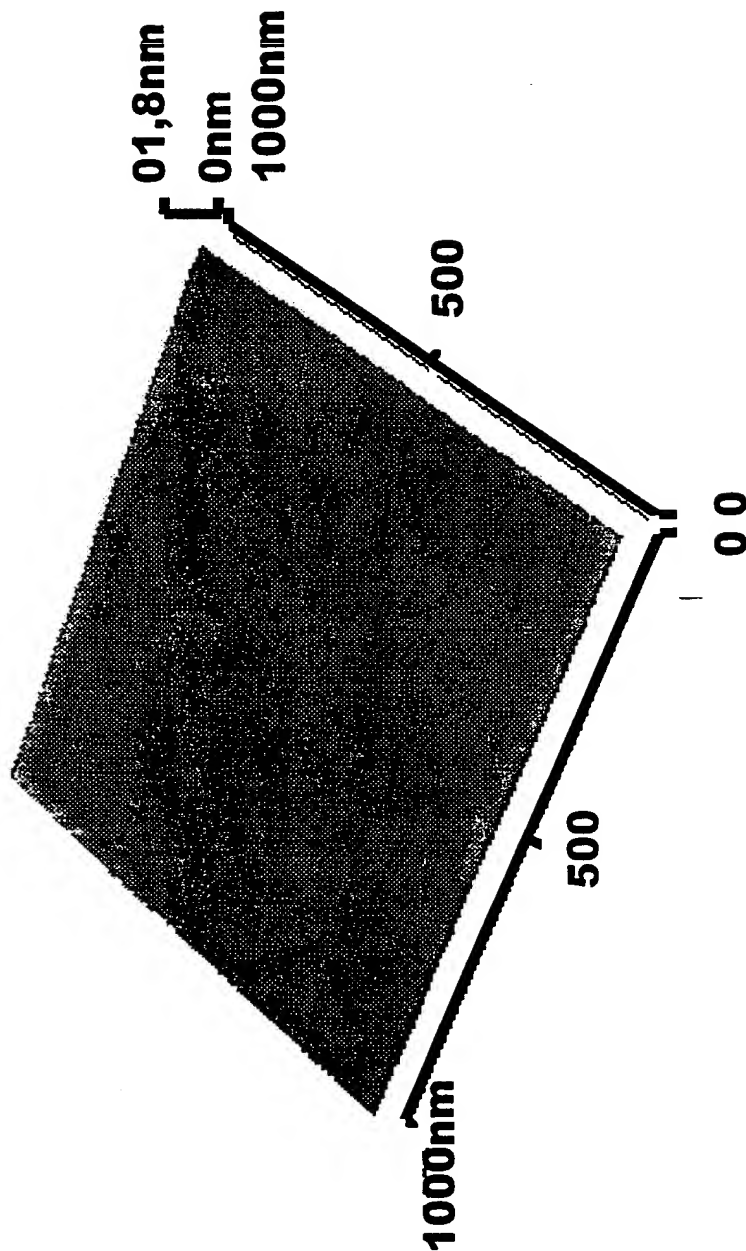


Fig. 4

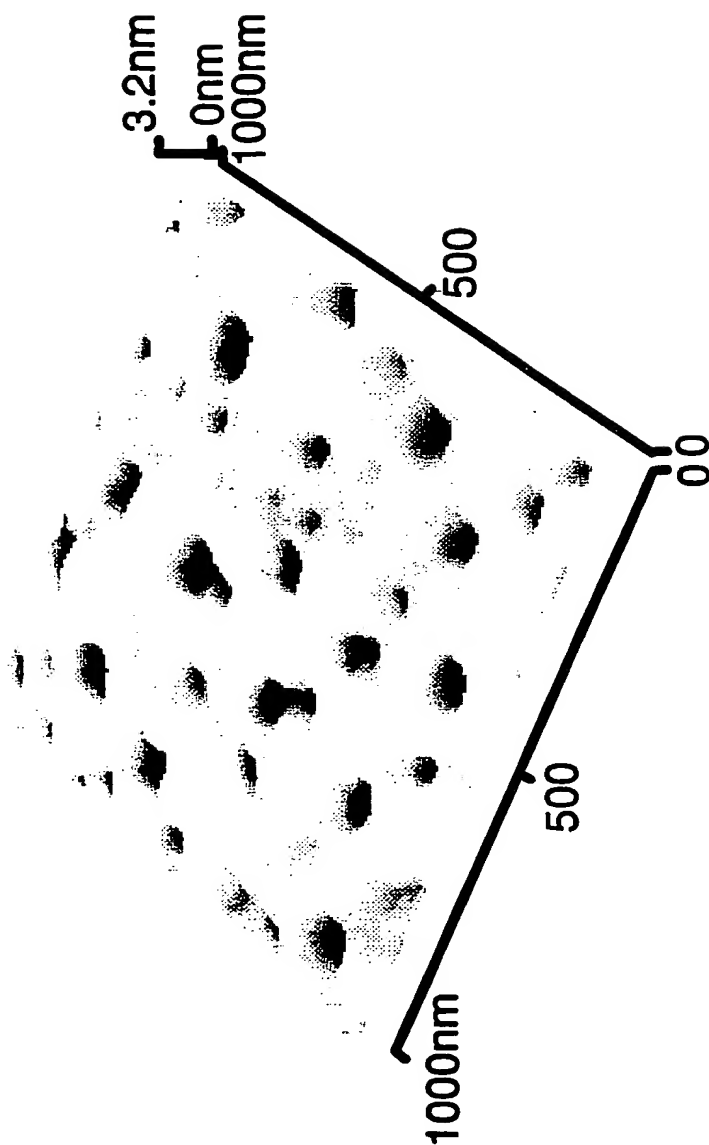


Fig. 5

INTERNATIONAL SEARCH REPORT

International Application No
PCT/EP 98/03885

A. CLASSIFICATION OF SUBJECT MATTER

IPC 6 H01L21/28 H01L21/324

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 6 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 5 279 973 A (SUIZU YASUMASA) 18 January 1994 see column 2, line 57 - column 5, line 34 ---	1-3,9
X	US 4 784 975 A (HOFMANN KARL ET AL) 15 November 1988	1-7,9,10
Y	see column 1, line 51 - line 57 see column 2, line 59 - column 3, line 2 see column 3, line 53 - column 4, line 4 see column 4, line 19 - line 21 see column 4, line 48 - line 63 see column 6, line 35 - column 7, line 16; figure 5 ---	8
Y	EP 0 742 593 A (NIPPON ELECTRIC CO) 13 November 1996 see column 11, line 17 - line 49 --- -/--	8



Further documents are listed in the continuation of box C.



Patent family members are listed in annex.

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Date of the actual completion of the international search

4 November 1998

Date of mailing of the international search report

17/11/1998

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INTERNATIONAL SEARCH REPORT

Int: onal Application No

PCT/EP 98/03885

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 4 626 450 A (TANI AKIHIKO ET AL) 2 December 1986 see column 3, line 41 - line 54; figure 3 see column 5, line 11 - line 18 see column 6, line 32 ---	1-3,9
X	NENYEI Z ET AL: "Gas flow engineering in rapid thermal processing" RAPID THERMAL AND INTEGRATED PROCESSING III SYMPOSIUM, RAPID THERMAL AND INTEGRATED PROCESSING III SYMPOSIUM, SAN FRANCISCO, CA, USA, 4-7 APRIL 1994, pages 401-406, XP002082958 1994, Pittsburgh, PA, USA, Mater. Res. Soc, USA see abstract see page 405 - page 406 -----	1,9,10

INTERNATIONAL SEARCH REPORT

information on patent family members

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